**Product data sheet** 

## 1. General description

PNP low V<sub>CEsat</sub> transistor in a medium power SOT89 (SC-62) package.

NPN complement: PBSS4540X.

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- · High efficiency leading to less heat generation.
- · AEC-Q101 qualified

## 3. Applications

- Supply line switching circuits
- · Battery management applications
- DC/DC converter applications
- Strobe flash units
- Medium power driver (e.g. relays, buzzers and motors).

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-40	V
I <sub>C</sub>	collector current		-	-	-4	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 10 ms	-	-	-10	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -5 A; $I_B$ = -500 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	45	75	mΩ



40 V, 5 A PNP low VCEsat (BISS) transistor

# 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		Ç
2	С	collector		в
3	В	base	3 2 1 SOT89	E sym132

# 6. Ordering information

#### **Table 3. Ordering information**

Type number	ber Package						
	Name	Description	Version				
PBSS5540X		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89				

## 7. Marking

### Table 4. Marking codes

Type number	Marking code[1]
PBSS5540X	%1G

[1] % = placeholder for manufacturing site code

**Product data sheet** 

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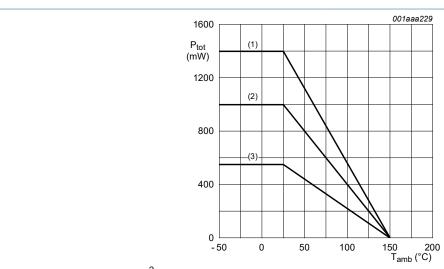
## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-40	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-40	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-6	V
I <sub>C</sub>	collector current			-	-4	Α
I <sub>CRM</sub>	repetitive peak collector current	$\delta \le 0.2$ ; $t_p \le 10 \text{ ms}$		-	-5	А
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 10 ms		-	-10	А
I <sub>B</sub>	base current			-	-1	Α
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-2	Α
P <sub>tot</sub>	total power dissipation		[1] [2]	-	2.5	W
		T <sub>amb</sub> ≤ 25 °C	[2]	-	0.55	W
			[3]	-	1	W
			[4]	-	1.4	W
			[5]	-	1.6	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Pulsed  $t_p \le 10 \text{ ms}$ ;  $\delta \le 0.2$
- [2] [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.
- Device mounted on a 7 cm<sup>2</sup> ceramic printed-circuit board, 1 cm<sup>2</sup> single-sided copper and tin-plated. [5]



- (1) FR4 PCB; 6 cm<sup>2</sup> mounting pad for collector (2) FR4 PCB; 1 cm<sup>2</sup> mounting pad for collector
- (3) FR4; standard footprint

#### **Power derating curves** Fig. 1.

40 V, 5 A PNP low VCEsat (BISS) transistor

### 9. Thermal characteristics

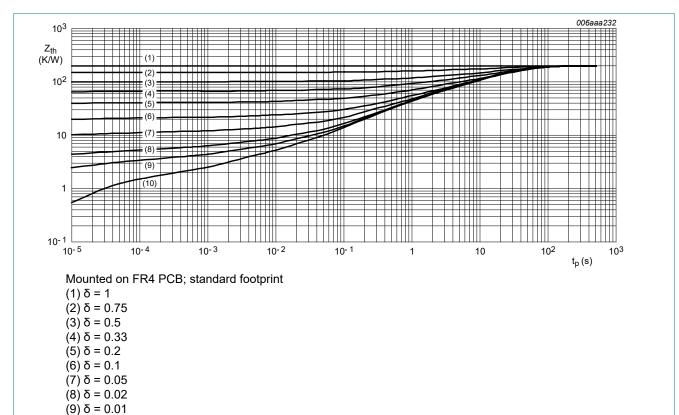
**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	[1 [3 [4	[1] [2]	-	-	50	K/W
	junction to ambient		[1]	-	-	225	K/W
			[3]	-	-	125	K/W
			[4]	-	-	90	K/W
			[5]	-	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Pulse test:  $t_p \le 10$  ms;  $\delta \le 0.2$ .

 $(10) \delta = 0$ 

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup> [3]
- [4]
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>. Device mounted on a 7 cm<sup>2</sup> ceramic printed-circuit board, 1 cm<sup>2</sup> single-sided copper and tin-plated.



Transient thermal impedance as a function of pulse duration; typical values

#### 40 V, 5 A PNP low VCEsat (BISS) transistor

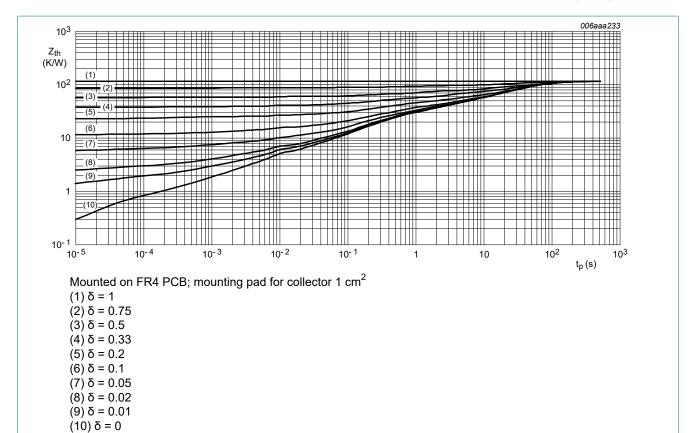
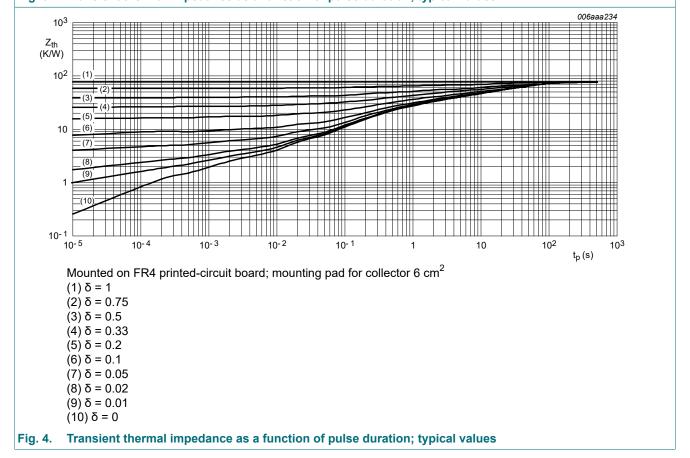


Fig. 3. Transient thermal impedance as a function of pulse duration; typical values



## 40 V, 5 A PNP low VCEsat (BISS) transistor

# 10. Characteristics

### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -30 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -0.5 A; T <sub>amb</sub> = 25 °C	250	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; $t_{p}$ ≤ 300 μs; pulsed; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -2 A; $t_{p}$ ≤ 300 μs; pulsed; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	150	-	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -5 A; $t_{p}$ ≤ 300 μs; pulsed; $\delta$ ≤ 0.02; $T_{amb}$ = 25 °C	50	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = -0.5 \text{ A}; I_B = -5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-120	mV
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -10 mA; T <sub>amb</sub> = 25 °C	-	-	-170	mV
		I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA; T <sub>amb</sub> = 25 °C	-	-	-160	mV
		$I_C$ = -4 A; $I_B$ = -200 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-340	mV
		$I_C = -5 \text{ A}; I_B = -500 \text{ mA}; t_p \le 300  \mu\text{s};$	-	-	-375	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	pulsed; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	45	75	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -4 A; $I_B$ = -200 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-1.1	V
		$I_C$ = -5 A; $I_B$ = -500 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-1.2	V
$V_{BEon}$	base-emitter turn-on voltage	V <sub>CE</sub> = -2 V; I <sub>C</sub> = -2 A; T <sub>amb</sub> = 25 °C	-	-	-1	V
т	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -0.1 A; f = 100 MHz; $T_{amb}$ = 25 °C	60	-	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	105	pF

### 40 V, 5 A PNP low VCEsat (BISS) transistor

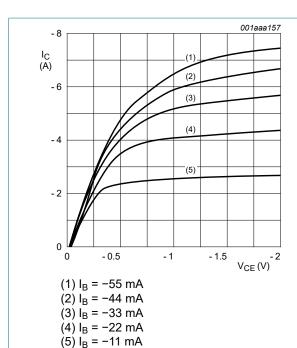


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

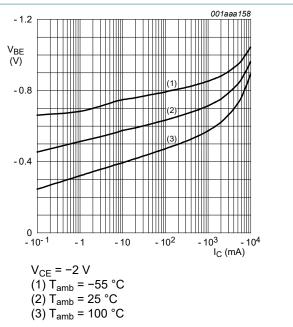
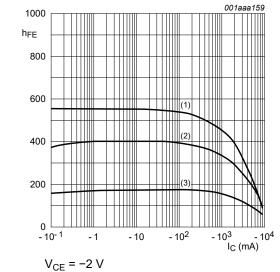
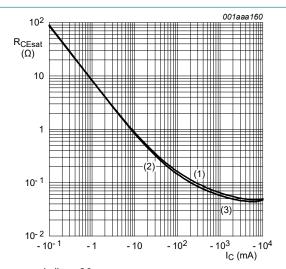


Fig. 6. Base-emitter voltage as a function of collector current; typical values



 $(1) T_{amb} = 100 °C$ (2) T<sub>amb</sub> = 25 °C (3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 7. DC current gain as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$ (1)  $T_{amb} = 100 \, ^{\circ}C$ (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig. 8. Equivalent on-resistance as a function of collector current; typical values

#### 40 V, 5 A PNP low VCEsat (BISS) transistor

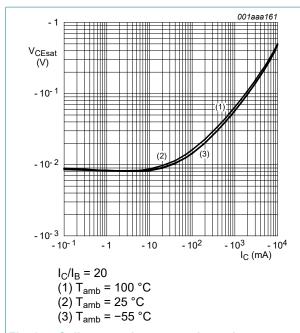


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

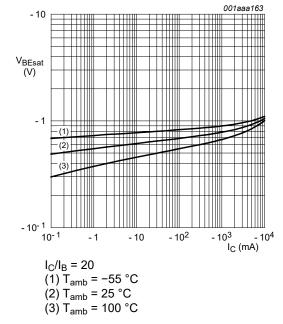


Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values

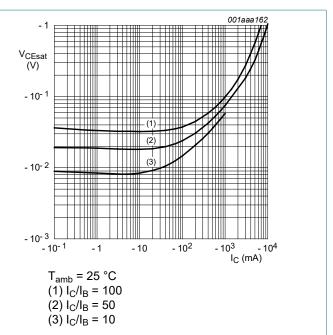


Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values

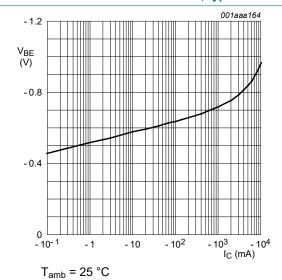
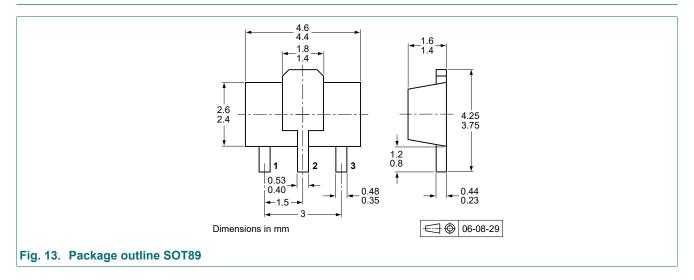


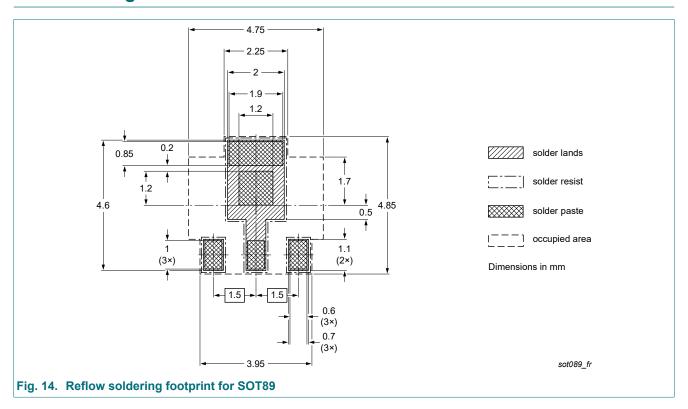
Fig. 12. Base-emitter voltage as a function of collector current; typical values

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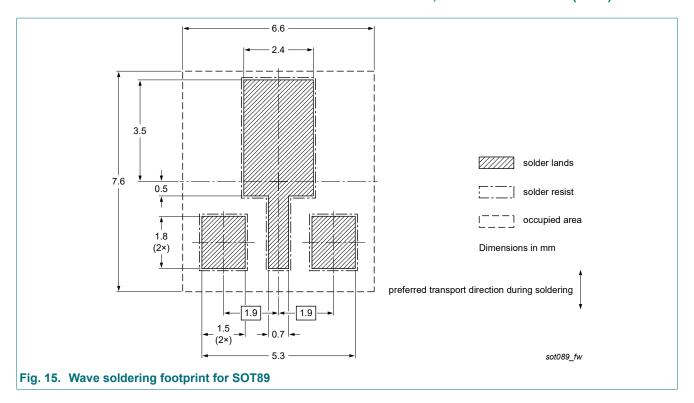
# 11. Package outline



## 12. Soldering



### 40 V, 5 A PNP low VCEsat (BISS) transistor



## 40 V, 5 A PNP low VCEsat (BISS) transistor

# 13. Revision history

#### **Table 8. Revision history**

Table of Novicion motory							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PBSS5540X v.4	20200415	Product data sheet	-	PBSS5540X v.3			
Modifications:	<ul> <li>Limiting value</li> </ul>	s at I <sub>CM</sub> : conditions corrected	·	·			
PBSS5540X v.3	20180320	Product data sheet	-	PBSS5540X v.2			
PBSS5540X v.2	20041104	Product data sheet	-	PBSS5540X v.1			
PBSS5540X v.1	20040115	Product data sheet	-	-			

### 40 V, 5 A PNP low VCEsat (BISS) transistor

## 14. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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